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(54) Title: TREATMENT METHOD AND DEVICE OF THE WORKING LAYER OF A MULTILAYER STRUCTURE

(57) Abstract: According to a first embodiment, the invention relates to a method for treating an electrically conductive working layer of a multilayer structure made from semiconductor materials, the structure including under said working layer an electrically insulating layer, said treatment being destined to constitute in said working layer at least one island surrounded by material of the electrically insulating layer, method including a wet chemical etching step of the working layer, method characterised in that prior to the wet etching step selective masking is realised on several regions of said working layer in order to constitute in this working layer several islands, each region masked from the layer corresponding to a respective island. The invention also proposes the application of such a method to the characterisation of the electrical properties of a structure, and an associated device.



WO 2005/088716 A2